

808 nm LD Epiwafer



EPIWAFERS FOR PHOTODETECTOR (PD)

EPIWAFERS FOR VISIBLE-LIGHT LASER DIODE (LD) and RCLED

EPIWAFERS FOR LASER DIODE

Descriptions

The 808 nm laser epiwafer adopts AlGaAs multiple quantum-well as the active layer. The maximum output power for fabricated laser can be 1mW. Good uniformity of wavelength around 2" wafer can be achieved.

Wafer Characterization

The epiwafers are characterized by PL, DCXD and CV tests. **Figure 1** through **Figure 3** show the typical results of our epiwafer. The PL wavelength mapping for 1200 points in the inner 40mm of a 2" wafer shows stand deviation of 1 nm.

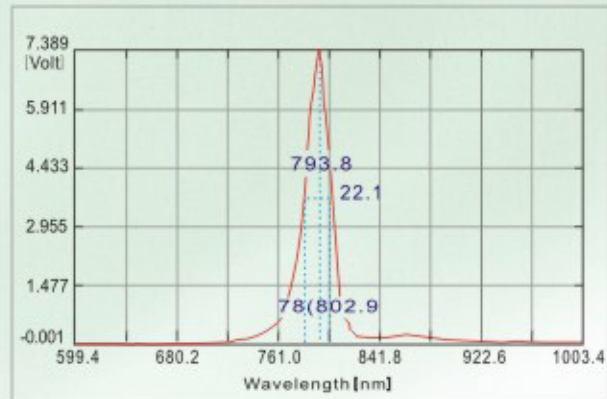


FIG.1

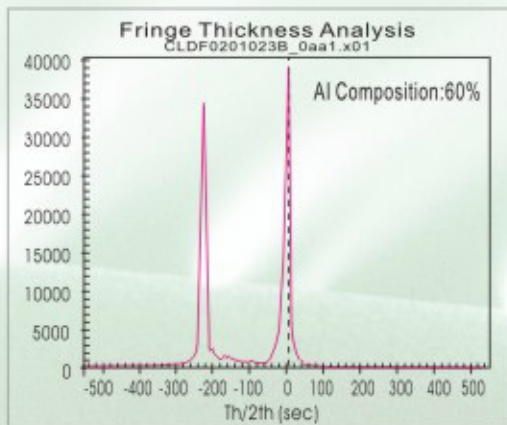


FIG.2

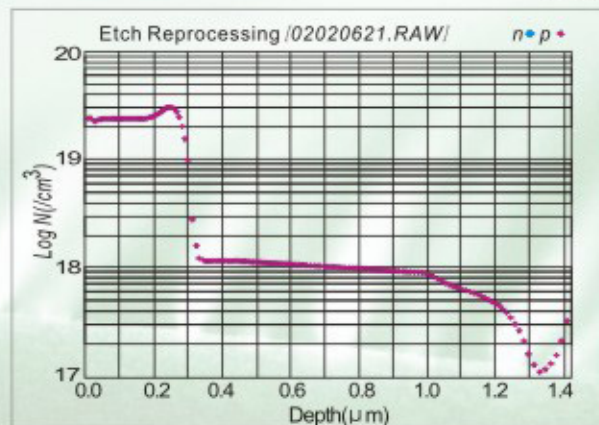


FIG.3

Device Performance

Characteristics	Symbol	Conditions	Typ.
Threshold Current	I_{th}	w/o coating	<150 mA
Operating Current	I_{OP}	@ 250 mW	546 mA
Wavelength	λ	@ 250 mW	~808 nm
Slope efficiency	η	w/o coating	~0.55 W/A

* Device structure: 50 μm x 700 μm BA Laser; as cleaved facet @ R.T.